

In the Claims

The following Listing of Claims replaces all prior versions in the application:

LISTING OF CLAIMS

1. (Currently amended) A method for manufacturing at least one electrode on a II-VI semiconducting material or a compound of the II-VI semiconductor material, the at least one electrode being in a metal for which the work function is substantially equal to or larger than that of the II-VI semiconducting material, this method being characterized in that the at least one electrode is formed by electrochemical deposition of the metal from a solution of a chloride of the metal in a ~~hydrochloric acid solution, wherein the hydrochloric acid solution consists essentially of pure hydrochloric acid, wherein pure hydrochloric acid solution consists essentially of pure hydrochloric acid diluted by less than about 80% water by weight~~ is the liquid which is obtained by dissolving about 37% to about 38% by weight of hydrogen chloride gas molecules in water.
2. (Previously presented) The method according to claim 1, wherein the metal is gold or platinum and a gold chloride solution or a platinum chloride solution in pure hydrochloric acid is used.
3. (Previously presented) The method according to claim 2, wherein a concentration of gold chloride or platinum chloride in pure hydrochloric acid is less than 5%.
4. (Currently Amended) The method according to claim 1, wherein a surface of the II-VI semiconducting material is prepared before the deposition in order to make this surface capable of fixing the metal.
5. (Currently Amended) The method according to claim 4, wherein the surface of the II-VI semiconducting material is chemically etched.

6. (Previously presented) The method according to claim 5, wherein the metal is gold or platinum, a gold or platinum chloride solution in pure hydrochloric acid is used and a solution of bromine and hydrochloric acid is used for the chemical etching.
7. (Previously presented) The method according to claim 1, wherein the II-VI semiconducting material is CdTe.
8. (Previously presented) The method according to claim 7, wherein the at least one electrode is formed on a compound of CdTe which is selected from CdZnTe, CdTe:Cl, CdTeSe:Cl, CdZnTe:Cl, CdTe:In, CdZnTe:In and CdHgTe.
9. (Previously presented) The method according to claim 6, wherein a solution of bromine and pure hydrochloric acid is used for the chemical etching.
10. (Canceled)
11. (New) The method according to claim 1, wherein a concentration of the chloride of the metal in pure hydrochloric acid is less than 5%.
12. (New) The method according to claim 5, wherein the material is rinsed in pure hydrochloric acid after chemically etching the surface.
13. (New) The method according to claim 1, wherein a rinse of the material is performed in hydrochloric acid and then in water, after electrochemical deposition of the metal is completed.